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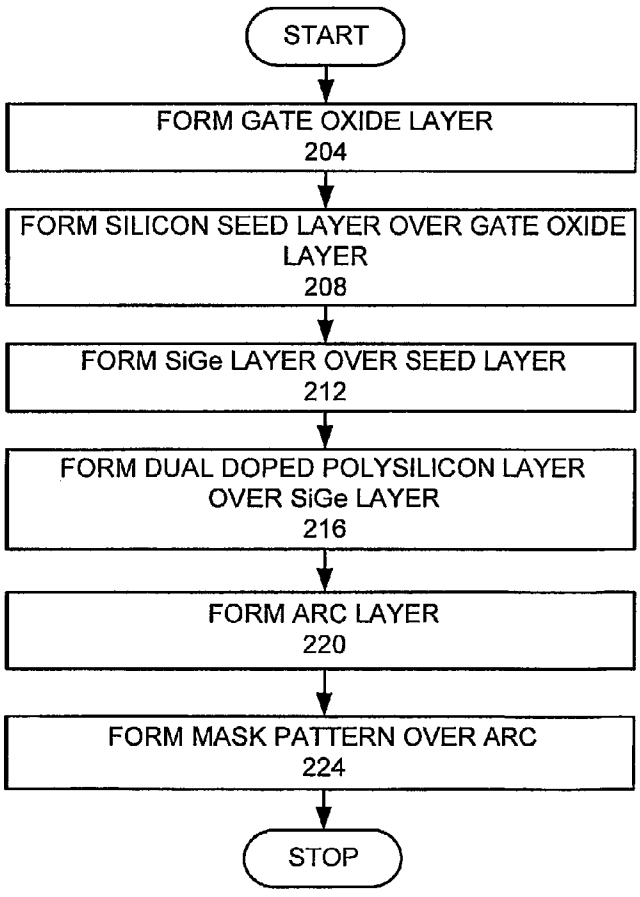
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(54) Title: DUAL DOPED POLYSILICON AND SILICON GERMANIUM ETCH



(57) Abstract: A method for etching a stack with at least one silicon germanium layer over a substrate in a processing chamber is provided. A silicon germanium etch is provided. An etchant gas is provided into the processing chamber, wherein the etchant gas comprises HBr, an inert diluent, and at least one of O_2 and N_2. The substrate is cooled to a temperature below 40° C. The etching gas is transformed to a plasma to etch the silicon germanium layer.

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